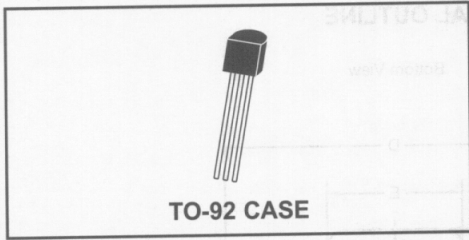


CQ92B
CQ92D
CQ92M
CQ92N

TRIAC

1.0 AMP, 200 THRU 800 VOLTS



DESCRIPTION:
The CENTRAL SEMICONDUCTOR CQ92B Series are epoxy molded silicon Triacs designed for full wave AC control applications featuring gate tripping in all four (4) quadrants.

MARKING CODE: FULL PART NUMBER

MAXIMUM RATINGS: (T_C=25°C unless otherwise noted)

	SYMBOL	CQ92B	CQ92D	CQ92M	CQ92N	UNITS
Peak Repetitive Off-State Voltage	V _{DRM}	200	400	600	800	V
RMS On-State Current (T _C =50°C)	I _{T(RMS)}		1.0			A
Peak One Cycle Surge (t=10ms)	I _{TSM}		20			A
I ² t Value for Fusing (t=10ms)	I ² t		2.0			A ² s
Peak Gate Power (tp=10µs)	P _{GM}		3.0			W
Average Gate Power Dissipation	P _{G (AV)}		0.2			W
Peak Gate Current (tp=10µs)	I _{GM}		1.2			A
Peak Gate Voltage (tp=10µs)	V _{GM}		8.0			V
Storage Temperature	T _{stg}		-40 to +150			°C
Junction Temperature	T _J		-40 to +125			°C
Thermal Resistance	θ _{JA}		180			°C/W
Thermal Resistance	θ _{JC}		90			°C/W

ELECTRICAL CHARACTERISTICS: (T_C=25°C unless otherwise noted)

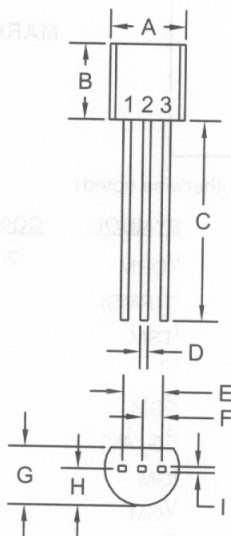
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{DRM}	Rated V _{DRM} , R _{GK} =1KΩ		5.0	µA
I _{DRM}	Rated V _{DRM} , R _{GK} =1KΩ, T _C =125°C		200	µA
I _{GT}	V _D =12V, QUAD I, II, III, IV		5.0	mA
I _H	I _T =100mA, R _{GK} =1KΩ		5.0	mA
V _{GT}	V _D =12V, QUAD I, II, III, IV		2.0	V
V _{TM}	I _{TM} =1.2A, tp=380µs		1.26	V
dv/dt	V _D =2/3 V _{DRM} , T _C =125°C	30		V/µs

CQ92B
 CQ92D
 CQ92M
 CQ92N

TRIAC

1.0 AMP, 200 THRU 800 VOLTS

TO-92 CASE - MECHANICAL OUTLINE



R1

DATA SHEETS

LEAD CODE:

- 1) MT1
- 2) GATE
- 3) MT2

MARKING CODE:
 FULL PART NUMBER

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)